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# Lecture17: CMOS amplifiers (4)

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# Read your textbook.

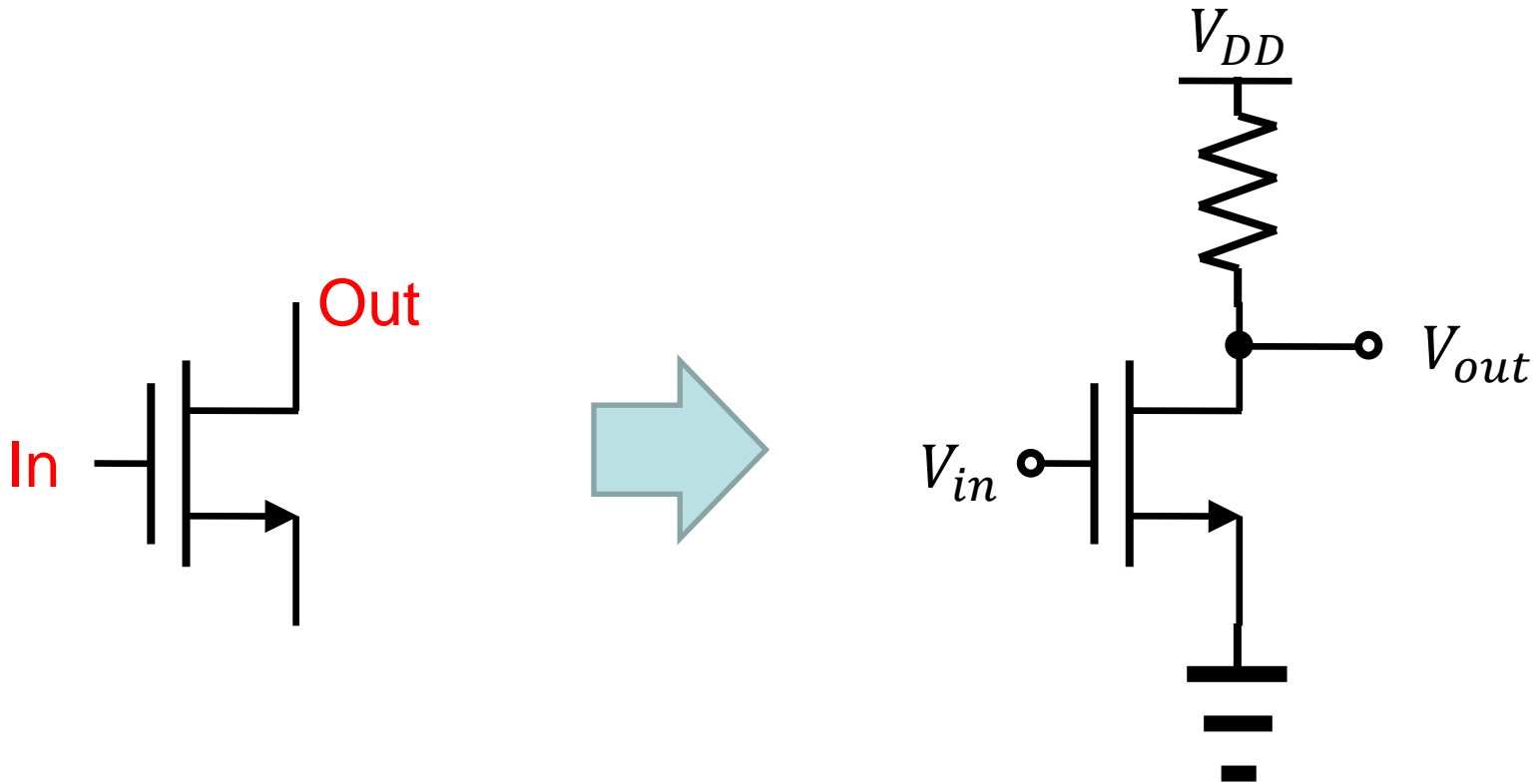
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- Reading your textbook is important.
- Today, we will try to cover up to p. 773.
  - Common-source
  - Just before “CS Stage with Biasing”
  - 17. 4. 4 (Common-gate) and 17. 4. 5 (Source-follower) will be covered on Wednesday.

# Common-source

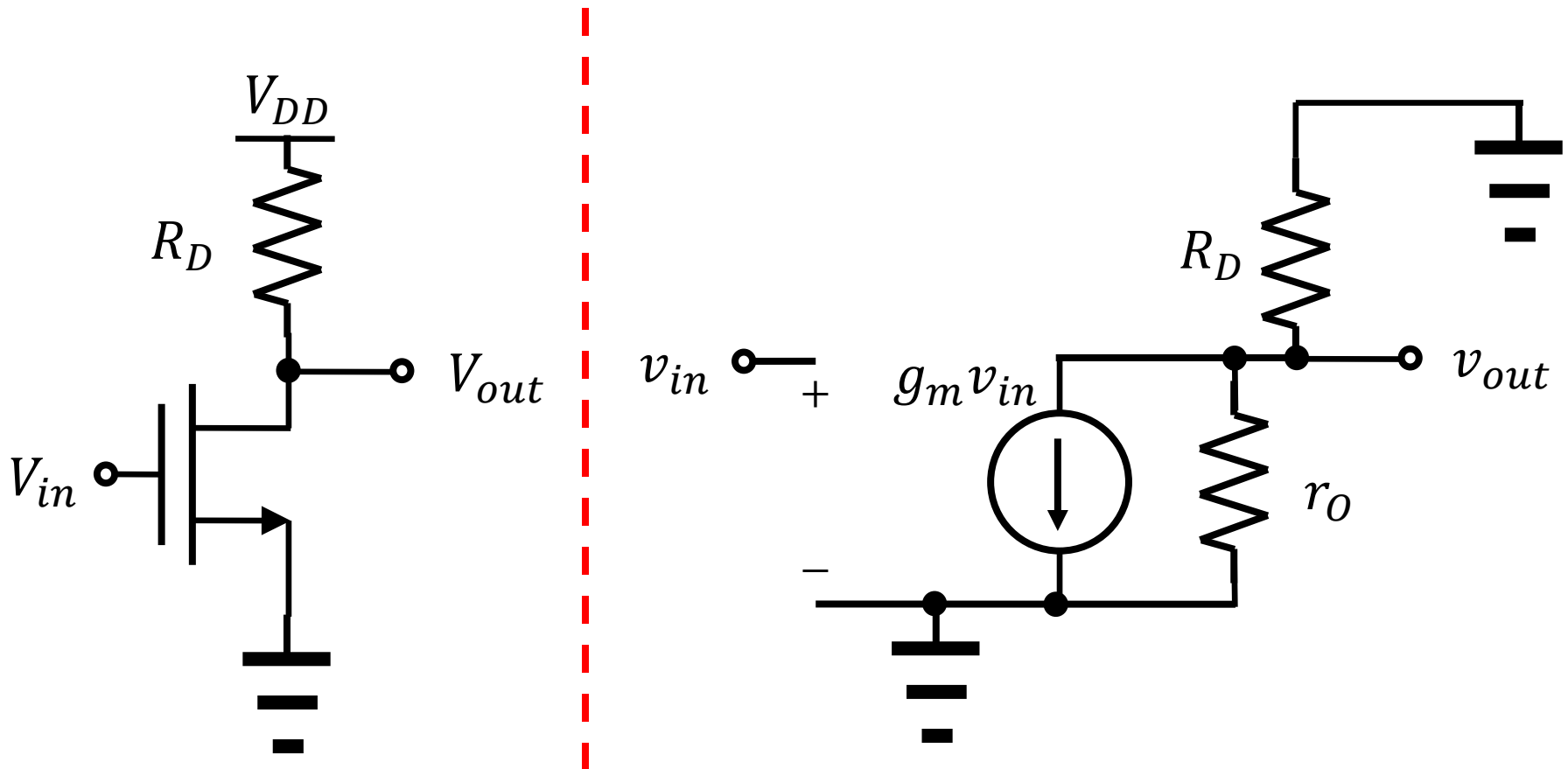
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- Source terminal is grounded.



# Small-signal model

- Let's draw the small-signal model together!



# Gain

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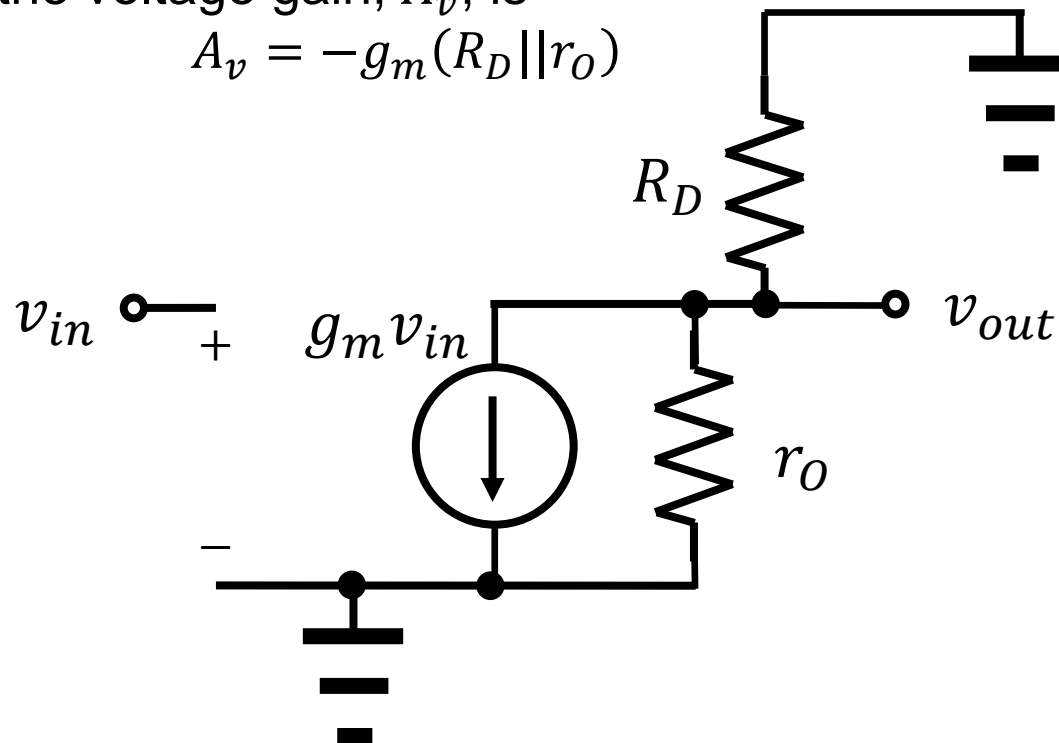
- Now, calculate the  $v_{out}$ .

- KCL for the  $v_{out}$  node gives

$$v_{out} = -g_m(R_D || r_o)v_{in}$$

- Therefore, the voltage gain,  $A_v$ , is

$$A_v = -g_m(R_D || r_o)$$



# Input/output impedances

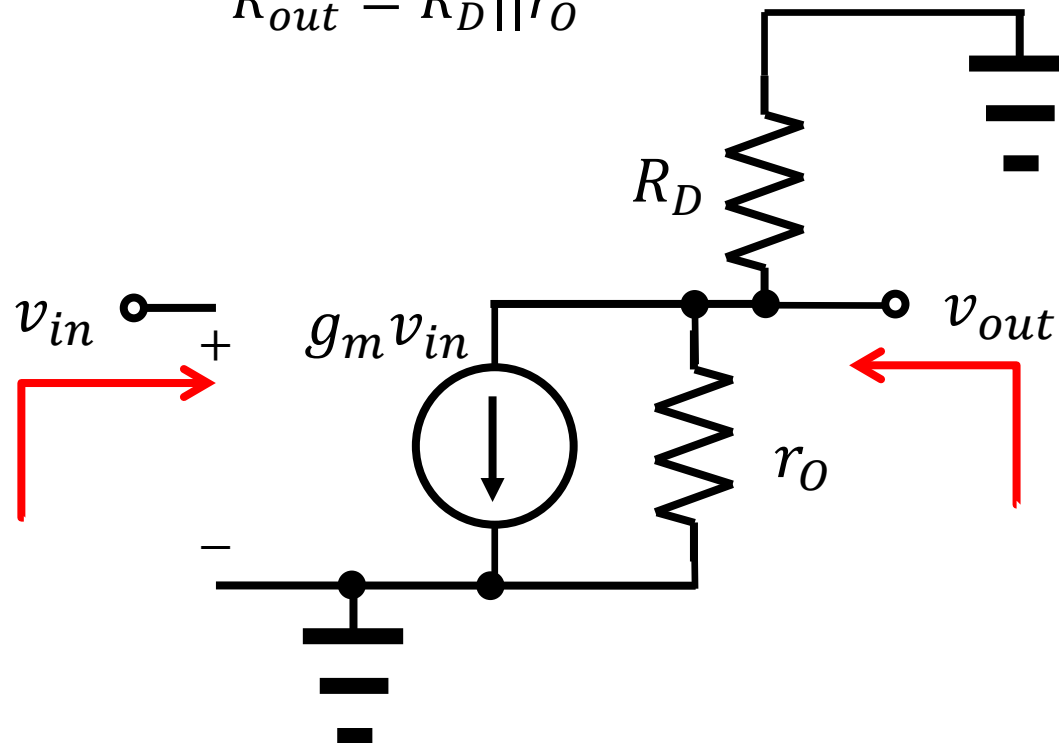
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- Input impedance

$$R_{in} = \infty$$

- Output impedance

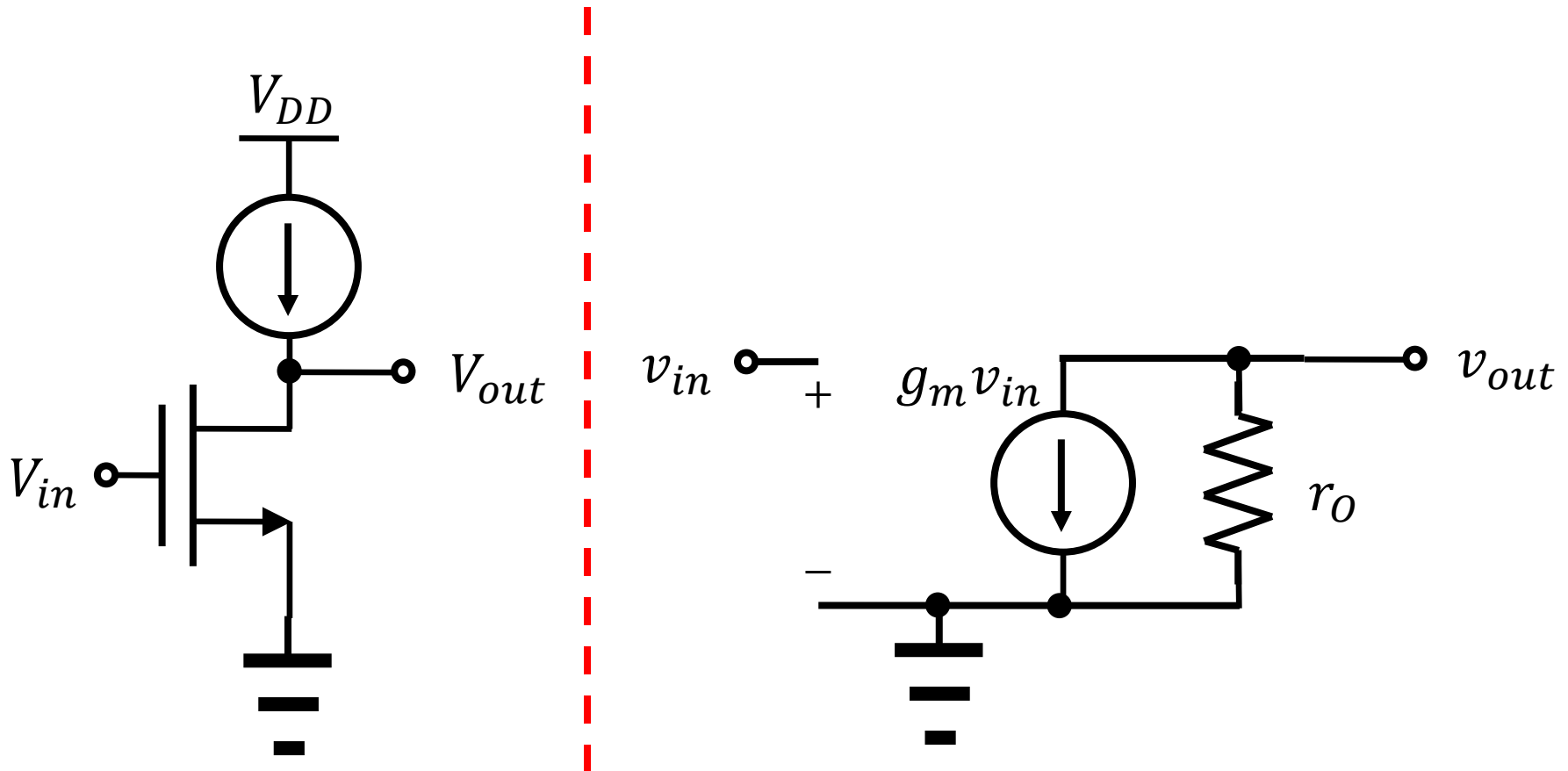
$$R_{out} = R_D || r_o$$



# Current-source load

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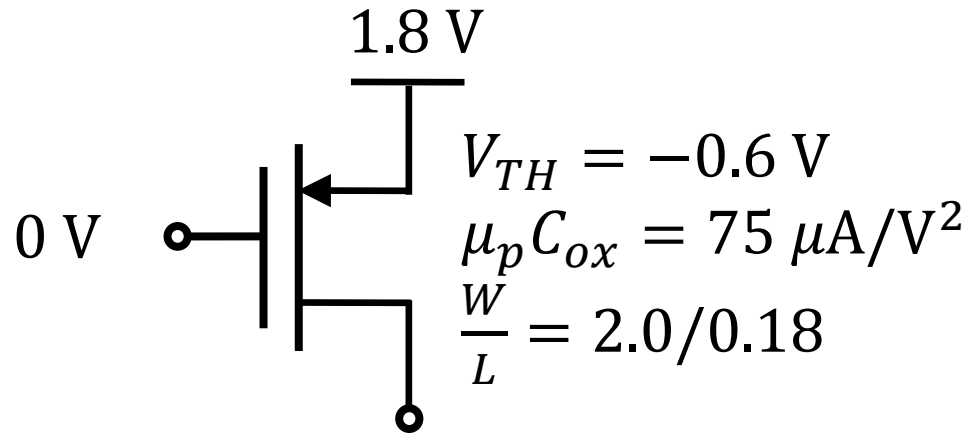
- When  $R_D \rightarrow \infty$ ,
  - The gain can be maximized.



# Biasing of PMOS devices

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- Let's recall the problem 18 of our mid-term exam.
  - The amount of “gate overdrive” is 1.2 V.
  - It is not 0.6 V.





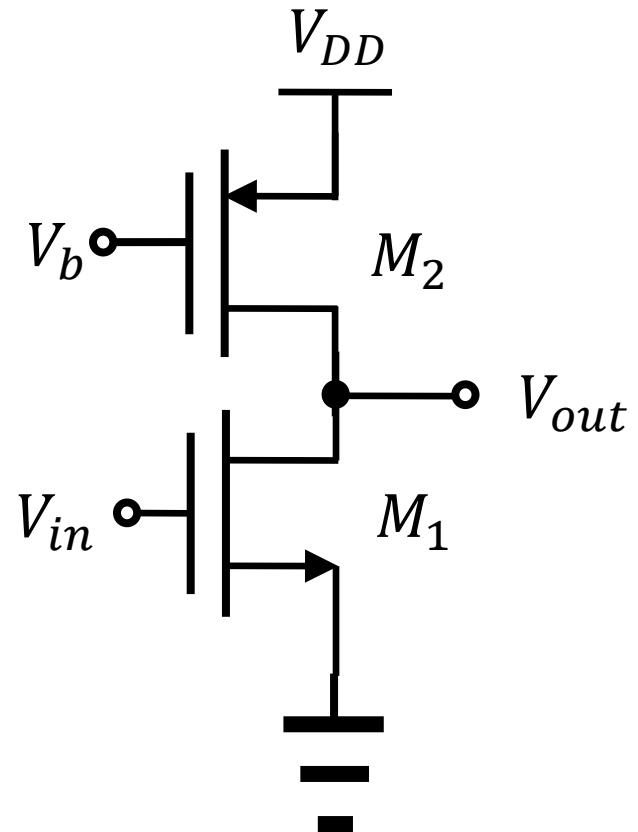
# Real current-source load

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- Use a PMOS as a current source.
  - It is not an ideal current source.

$$v_{out} = -g_{m1}(r_{O1}||r_{O2})v_{in}$$

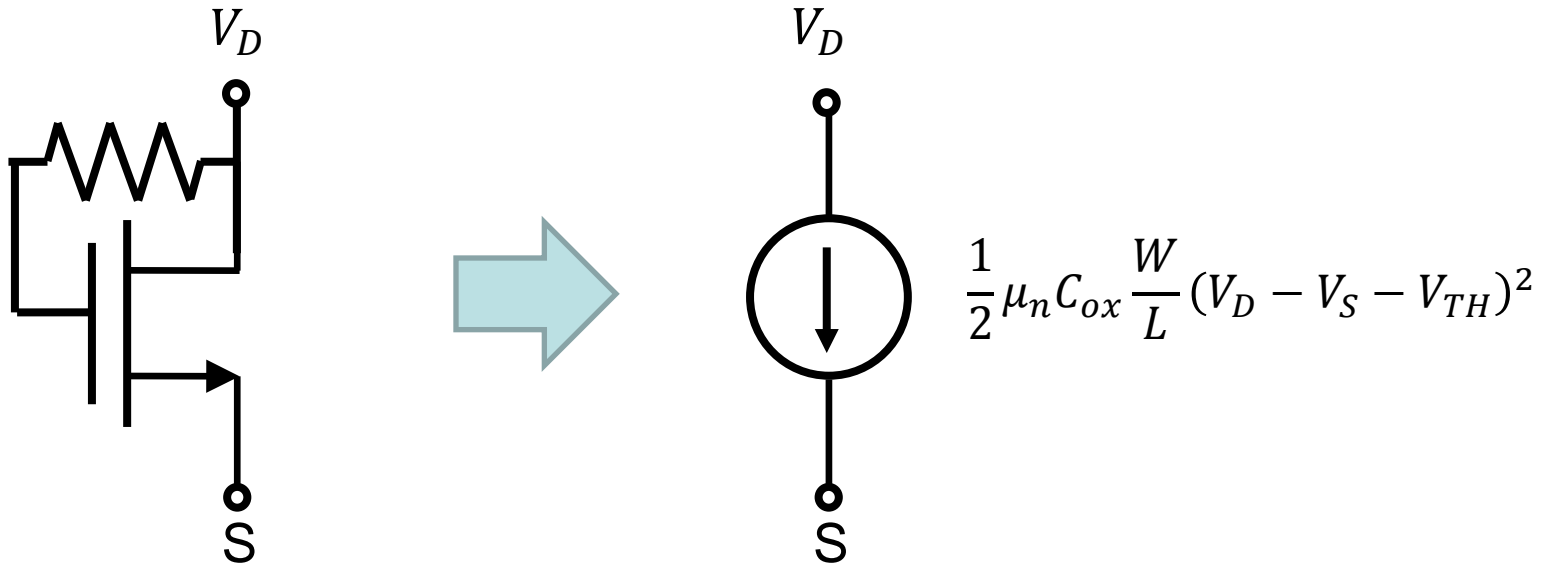
$$A_v = -g_{m1}(r_{O1}||r_{O2})$$



# Self-biasing

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- Already covered in Example 6.13.
  - Always in the saturation region.



Gate and drain are tied.

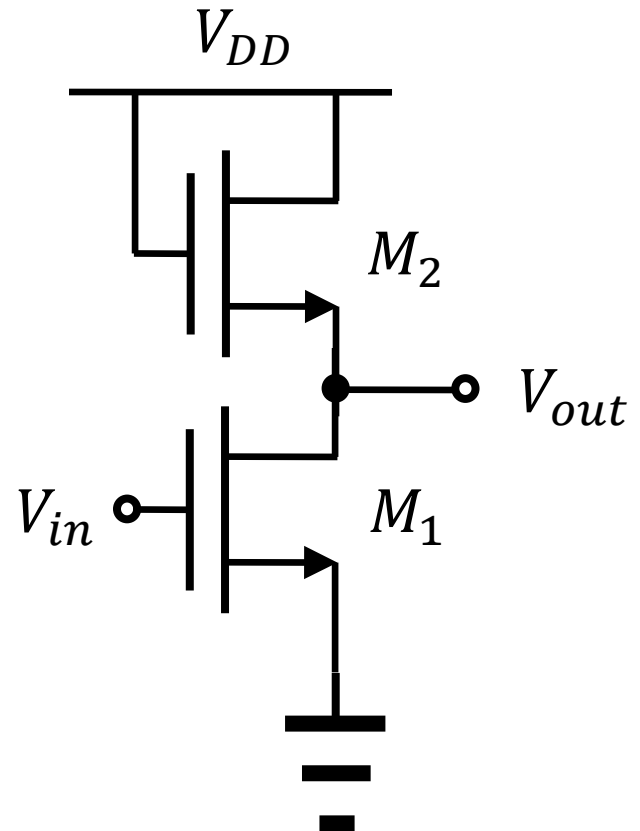
# In this case,

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- Use a diode-connected load.
  - It is not an ideal current source.

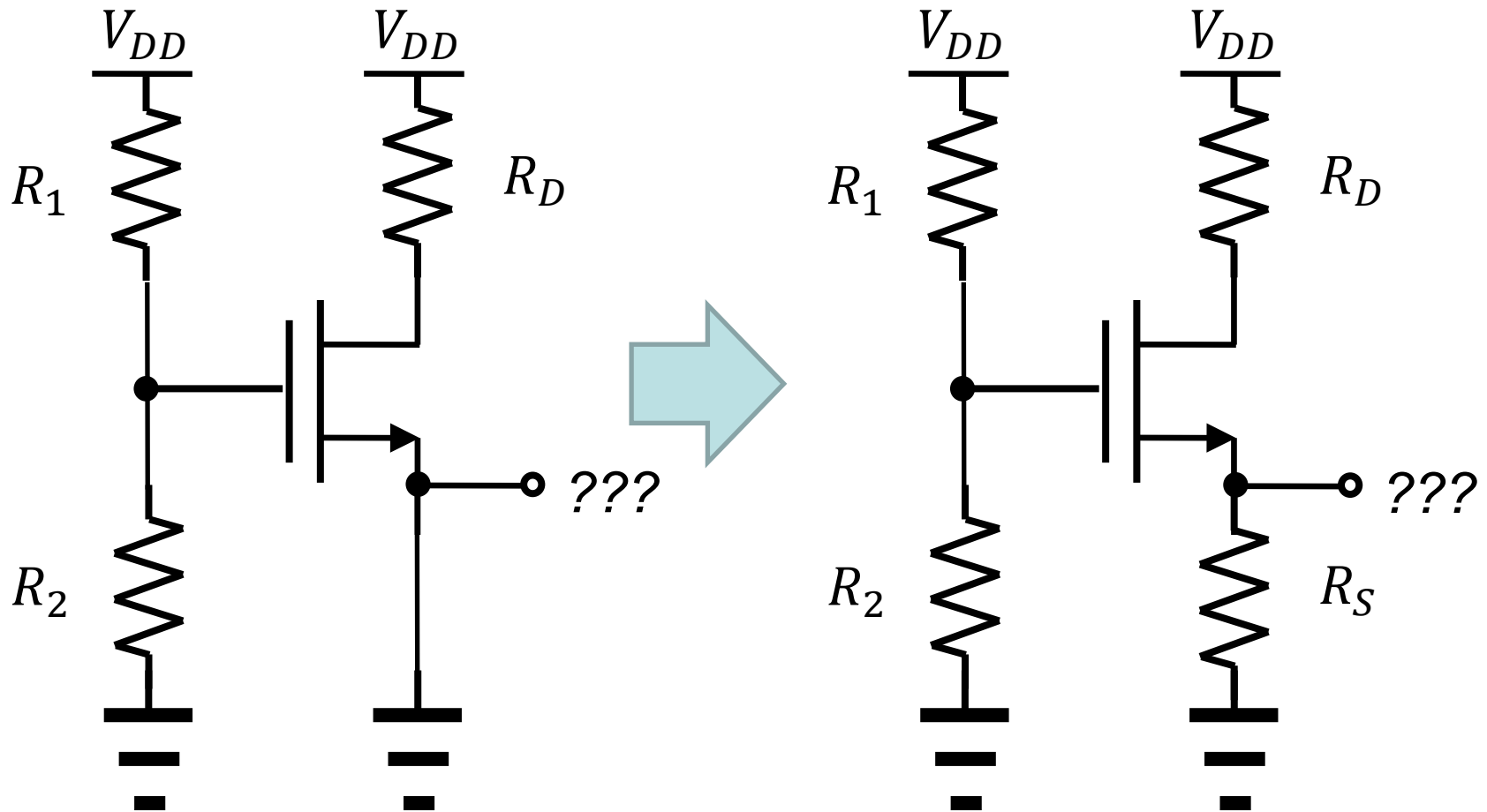
$$v_{out} = -g_{m1} \left( r_{O1} \parallel \frac{1}{g_{m2}} \parallel r_{O2} \right) v_{in}$$

$$A_v = -g_{m1} \left( r_{O1} \parallel \frac{1}{g_{m2}} \parallel r_{O2} \right)$$



# Source degeneration (1/2)

- A resistor placed in series with the source terminal



# Source degeneration (2/2)

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- Now we have to find the source voltage.
  - (Saturation current of the MOSFET) = (Current flowing through  $R_S$ )
  - After a simple manipulation, we can find

$$V_S = V_G + V_1 - V_{TH} - \sqrt{V_1^2 + 2(V_G - V_{TH})V_1}$$

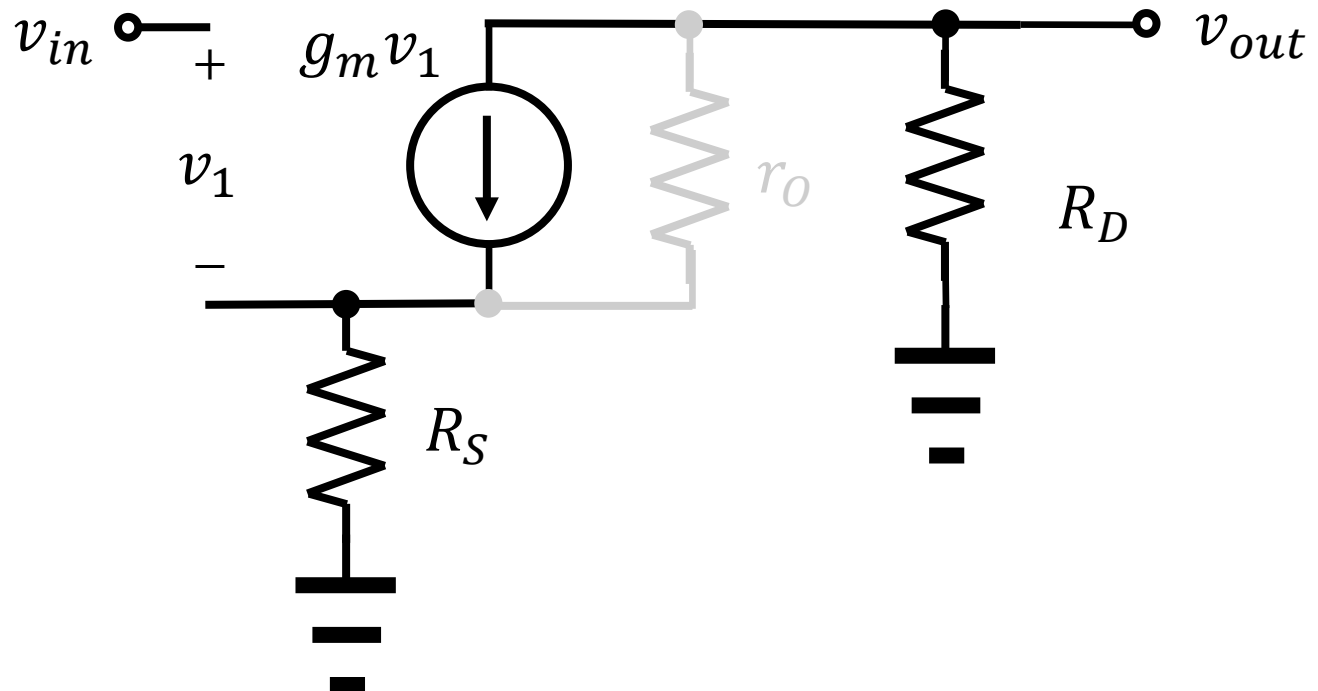
- Here,

$$V_1 = \frac{1}{\mu_n C_{ox} \frac{W}{L} R_S}$$

# Effect of $R_S$ (1/2)

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- Reduction of the gate-source voltage
  - Therefore, also reduction of the gain.
- For a while, neglect the channel-length modulation.

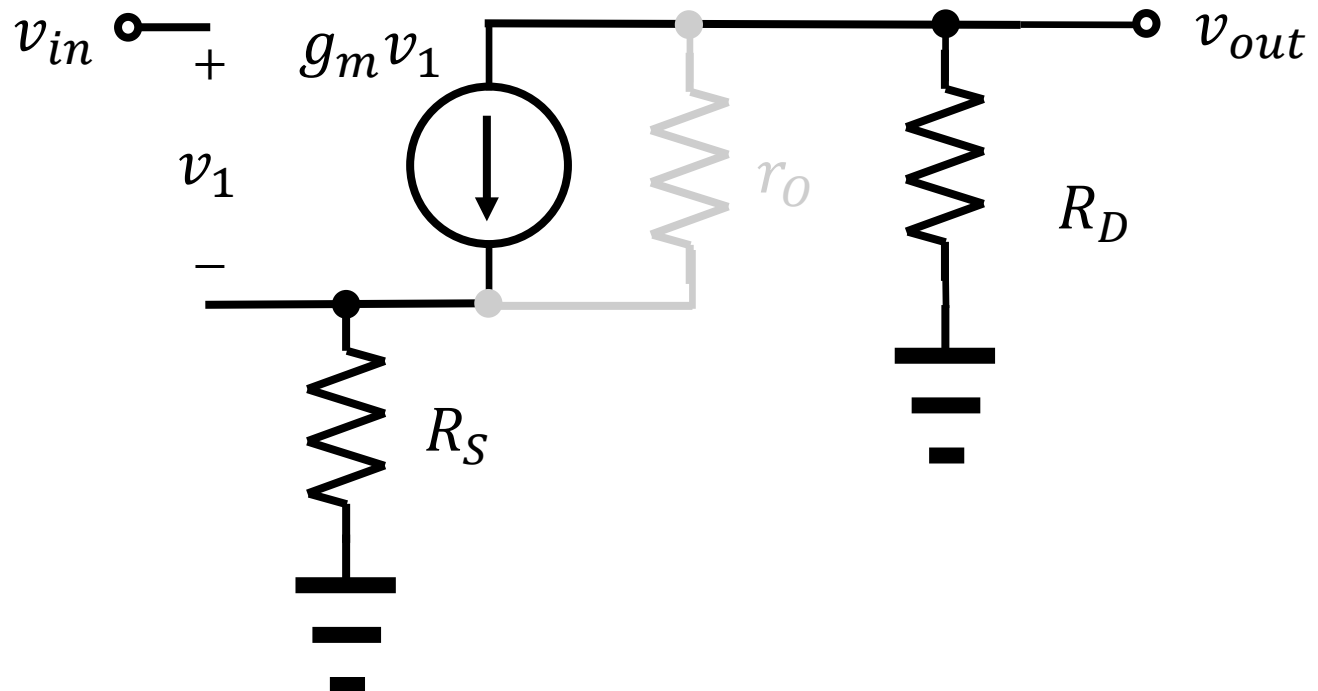


# Effect of $R_S$ (2/2)

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- After a simple manipulation,

$$A_v = -\frac{g_m R_D}{1 + g_m R_S}$$

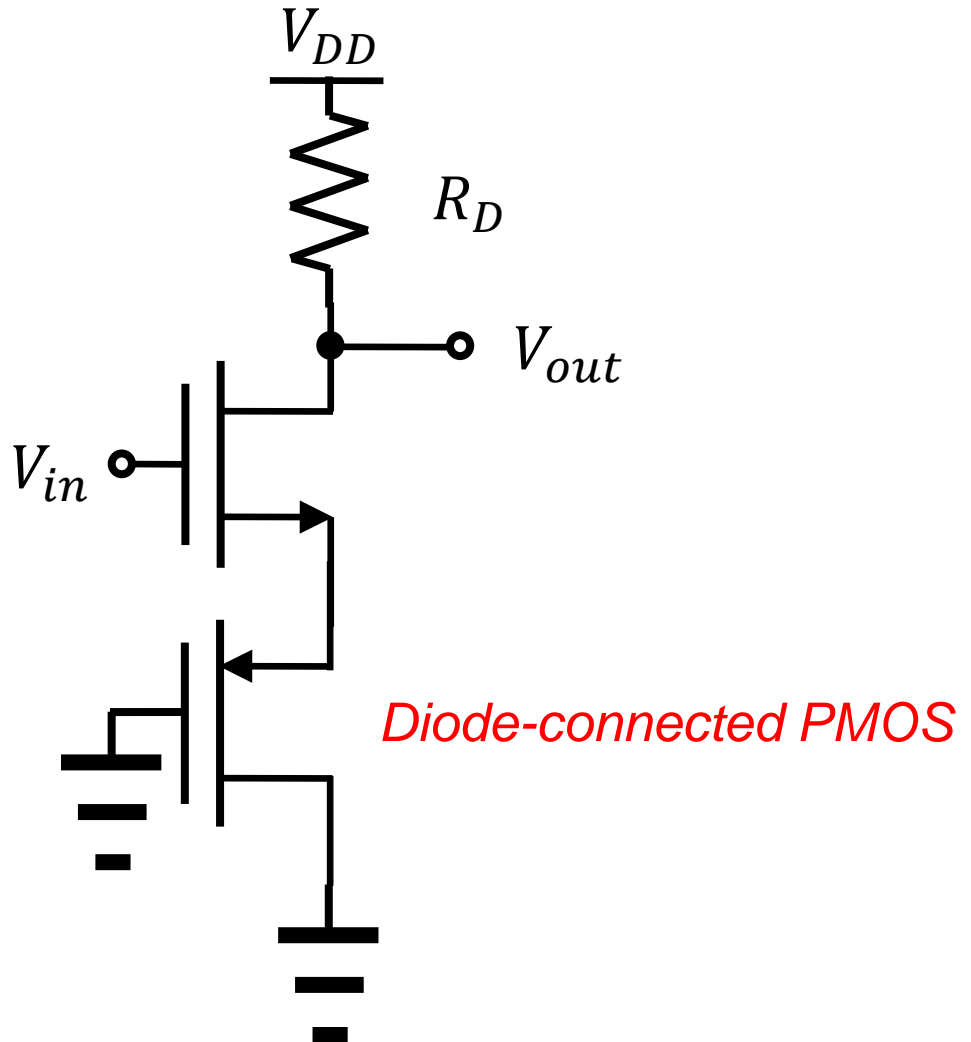


# Example 17.20

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- CS with degeneration

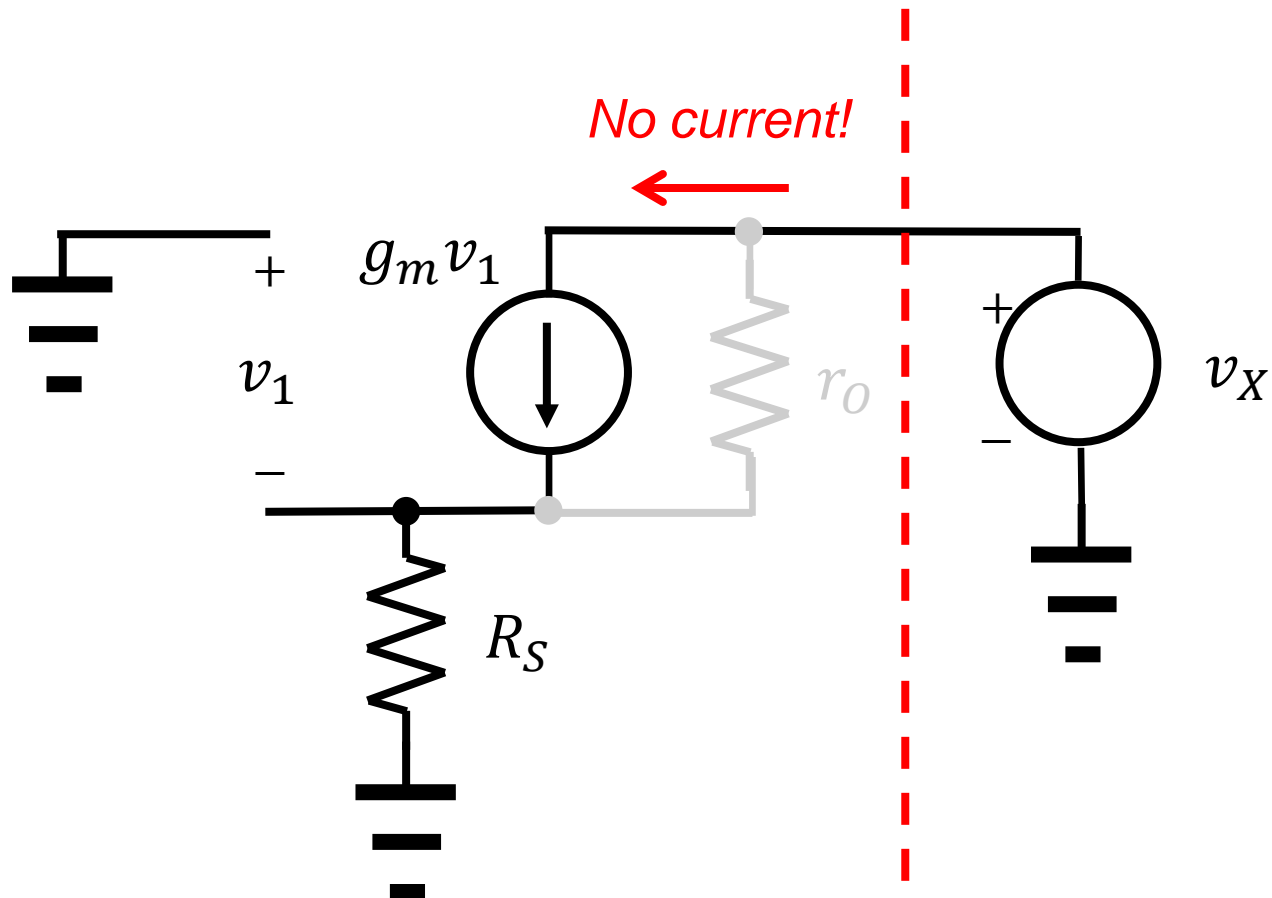
$$A_v = -\frac{R_D}{\frac{1}{g_{m1}} + \frac{1}{g_{m2}}}$$





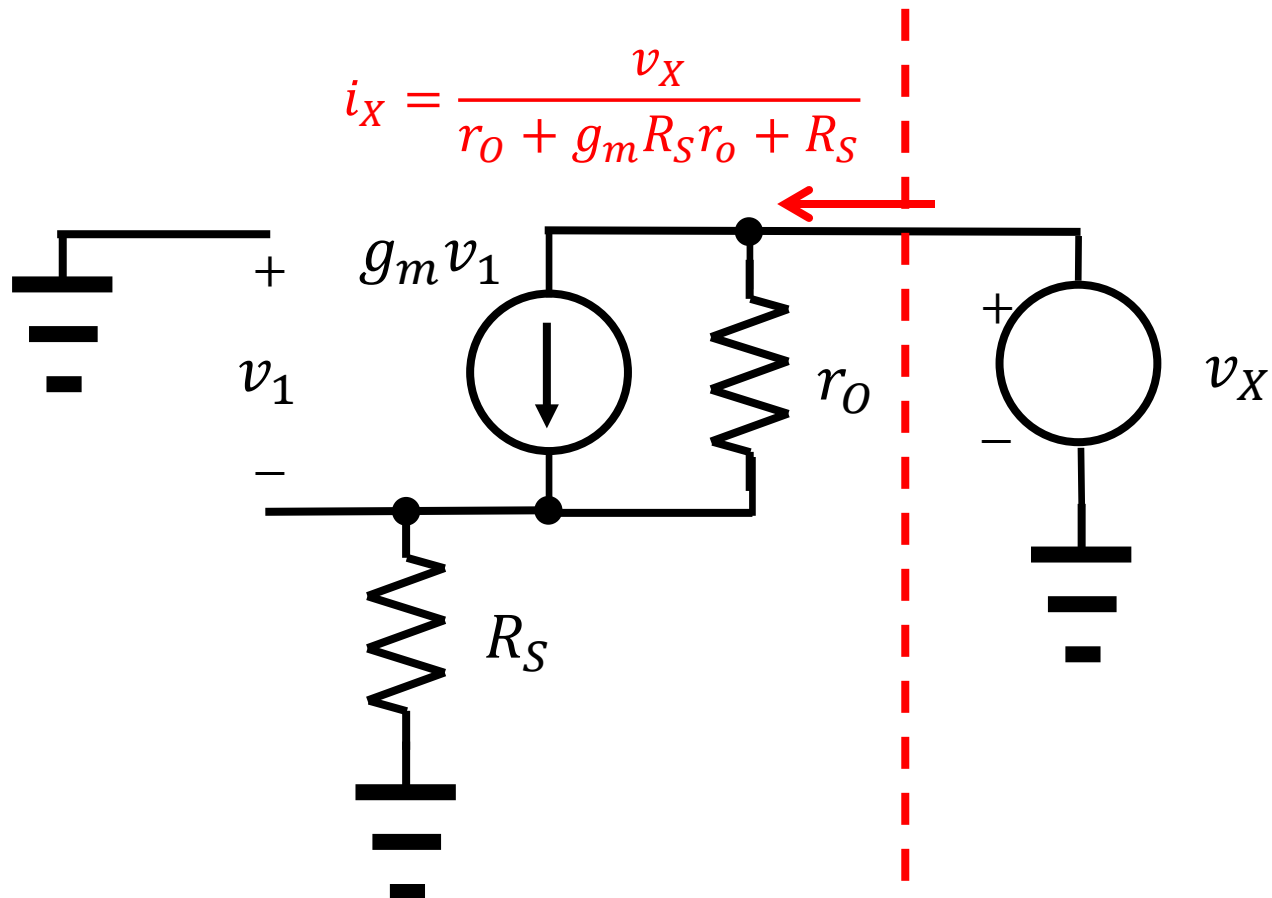
# Output impedance of CS (1/2)

- Still neglecting the channel-length modulation
  - No current!



# Output impedance of CS (2/2)

- Now considering the channel-length modulation
  - Output resistance is  $r_o + (g_m r_o + 1)R_S$ .



# Examples 17.23 and 17.24

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- Compute the output resistance.
  - What is the difference?

